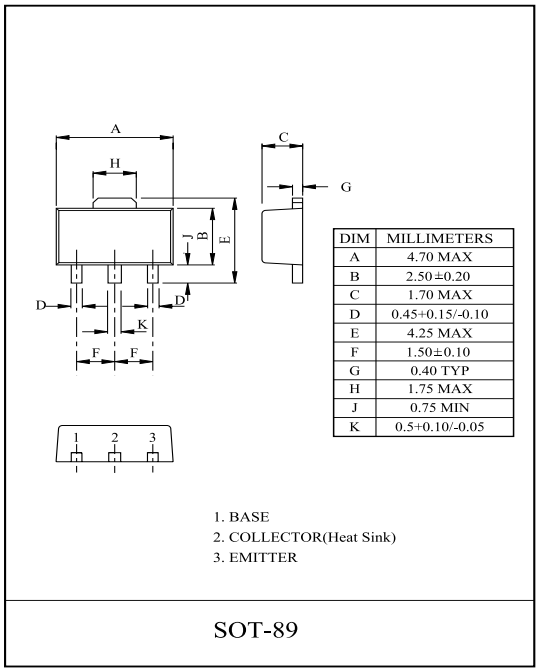
PXTA44

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH VOLTAGE APPLICATION.

FEATURES

· High Breakdown Voltage.



DIM	MILLIMETERS
A	4.70 MAX
B	2.50±0.20
C	1.70 MAX
D	0.45+0.15/-0.10
E	4.25 MAX
F	1.50±0.10
G	0.40 TYP
H	1.75 MAX
J	0.75 MIN
K	0.5+0.10/-0.05

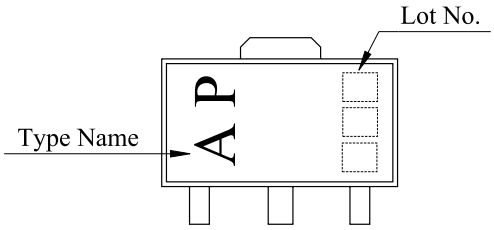
SOT-89

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	500	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	300	mA
Collector Power Dissipation	P_C	500	mW
	P_C*	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

* : Mounted on ceramic substrate(250㎟×0.8t)

Marking

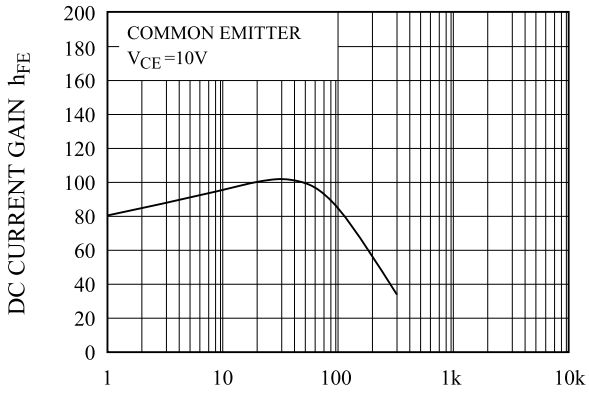


ELECTRICAL CHARACTERISTICS (Ta=25℃)

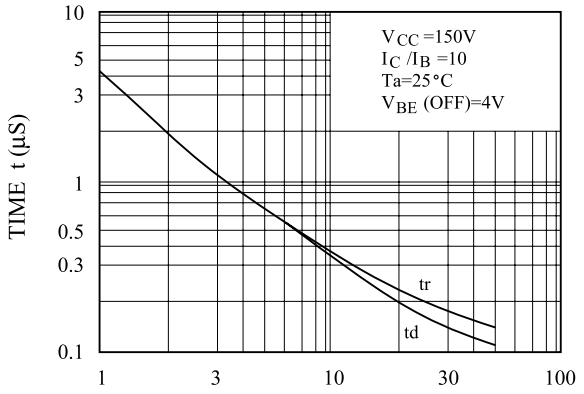
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100 μA, I_E=0	500	-	-	V
Collector-Emitter Breakdown Voltage (1)	$V_{(BR)CEO}$	I_C=1mA, I_B=0	400	-	-	V
Collector-Emitter Breakdown Voltage (2)	$V_{(BR)CES}$	I_C=100 μA, I_B=0	400	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10 μA, I_C=0	6.0	-	-	V
Collector Cut off Current (1)	I_{CBO}	V_{CB}=400V, I_E=0	-	-	100	nA
Collector Cut off Current (2)	I_{CES}	V_{CE}=400V, I_B=0	-	-	500	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0	-	-	100	nA
DC Current Gain *	h_{FE}	V_{CE}=10V, I_C=1mA	40	-	-	
		V_{CE}=10V, I_C=10mA	50	-	200	
		V_{CE}=10V, I_C=50mA	45	-	-	
		V_{CE}=10V, I_C=100mA	40	-	-	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$	I_C=10mA, I_B=1mA	-	-	0.5	V
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	I_C=10mA, I_B=1mA	-	-	0.75	V

*Pulse Test : Pulse Width≦300 μS, Duty Cycle≦2.0%

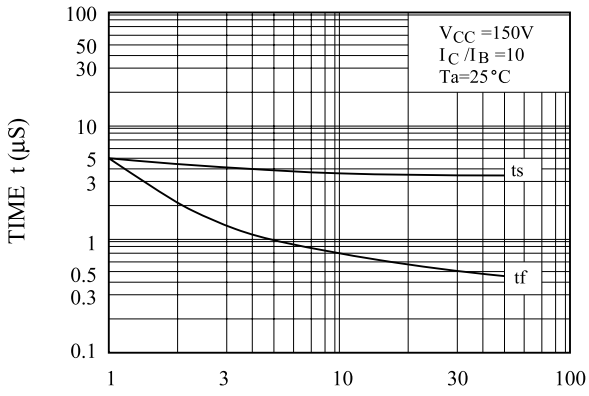
h_{FE} - I_C



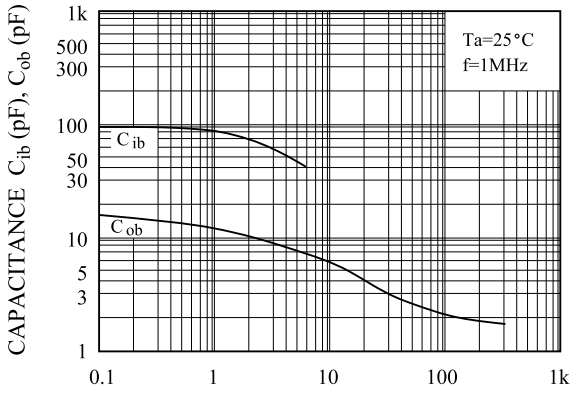
TURN-ON SWITCHING CHARACTERISTICS



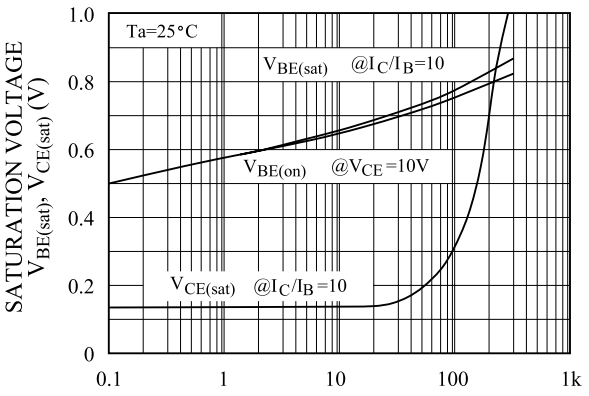
TURN-OFF SWITCHING CHARACTERISTICS



C_{ib}, C_{ob} - V_{CB}



$V_{BE(sat)}$, $V_{CE(sat)}$ - I_C



COLLECTOR SATURATION REGION